

## 15kV 30mA HIGH VOLTAGE DIODES

HVRT is high reliability resin molded type high voltage diode in small size package which is sealed a multilayed mesa type silicon chip by epoxy resin.

**■ Features**

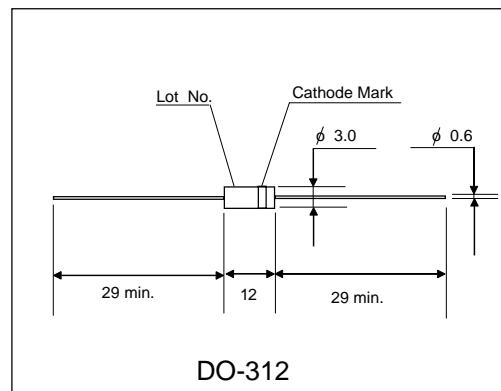
- High speed switching
- Low VF
- High surge resistivity for CRT discharge
- High reliability design
- Ultra small pakage

**■ Applications**

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power

**■ Maximum Ratings and Characteristics**

- Absolute Maximum Ratings

**■ Outline Drawings : mm****■ Cathode Mark**

Type	Mark
HVRT150	

**■ Maximum Ratings and Characteristics**

- Absolute Maximum Ratings

Items	Symbols	Condition	HVRT150	Units
Repetitive Peak Renerse Voltage	V <sub>RRM</sub>		15	kV
Average Output Current	I <sub>O</sub>	T <sub>a</sub> =25°C, Resistive Load	30	mA
Suege Current	I <sub>FSM</sub>	10mS Sine-half wave peak value	3.0	A <sub>peak</sub>
Junction Temperature	T <sub>J</sub>		125	°C
Allowable Operation Case Temperature	T <sub>C</sub>		125	°C
Storage Temperature	T <sub>stg</sub>		-40 to +125	°C

- Electrical Characteristics (T<sub>a</sub>=25°C Unless otherwise specified )

Items	Symbols	Conditions	HVRT150	Units
Maximum Forward Voltage Drop	V <sub>F</sub>	at 25°C, I <sub>F</sub> = I <sub>F(AV)</sub>	30	V
Maximum Reverse Current	I <sub>R1</sub>	at 25°C, V <sub>R</sub> =15kV	2.0	μA
	I <sub>R2</sub>	at 100°C, V <sub>R</sub> =15kV	20	μA
Maximum Reverse Recovery Time	T <sub>rr</sub>	at 25°C, I <sub>f</sub> =2mA, I <sub>R</sub> =4mA	100	nS
Junction Capacitance	C <sub>j</sub>	at 25°C, V <sub>R</sub> =0V, f=1MHz	1.0	pF